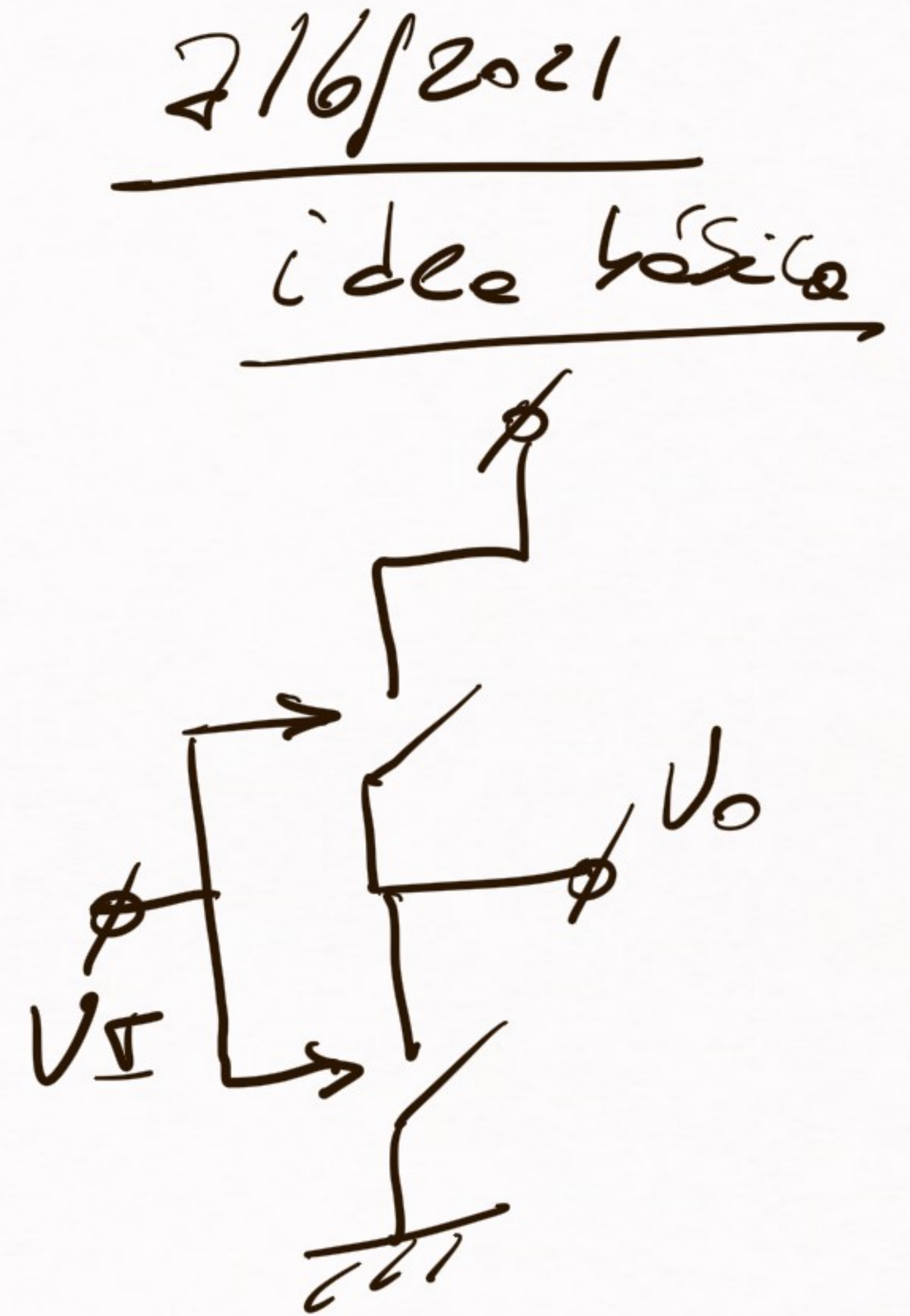
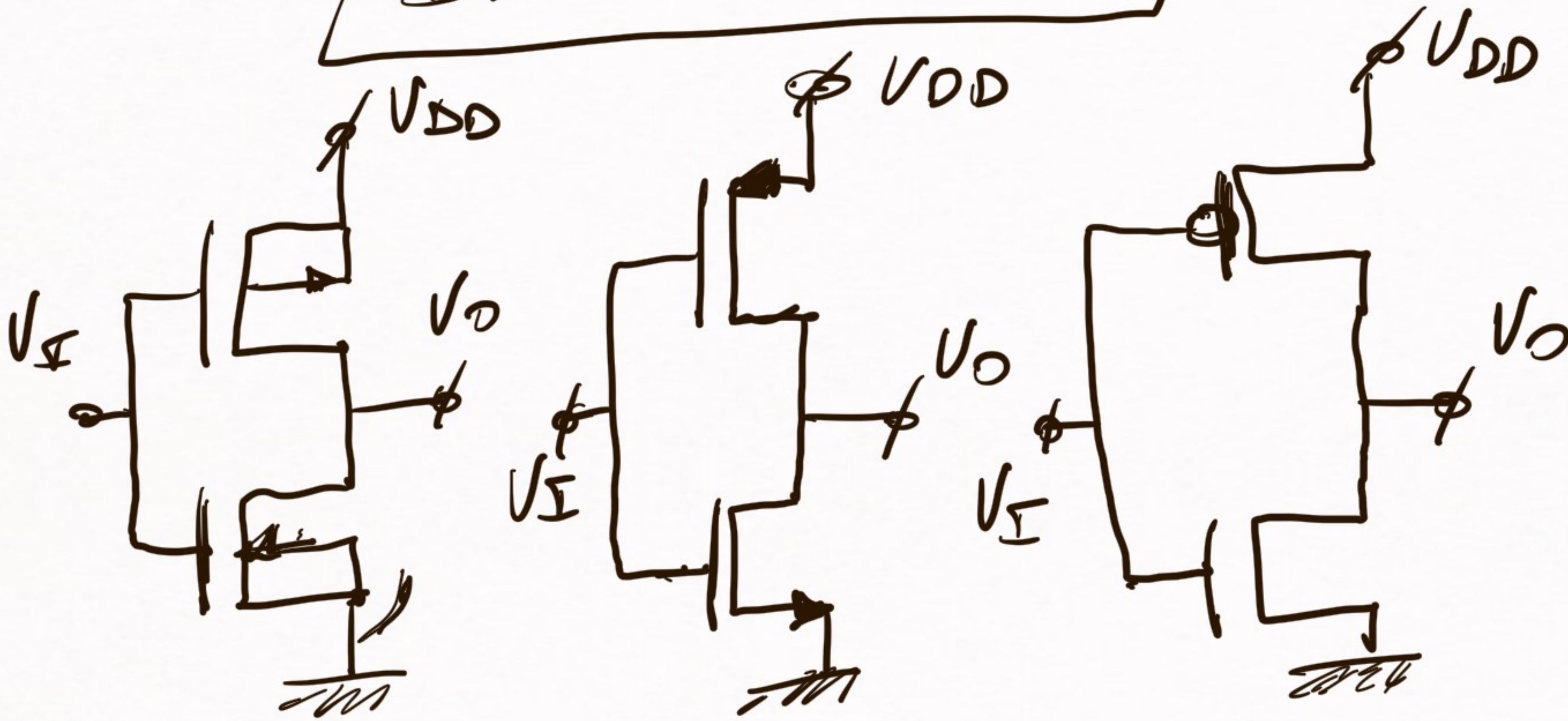


INVERSOR CMOS



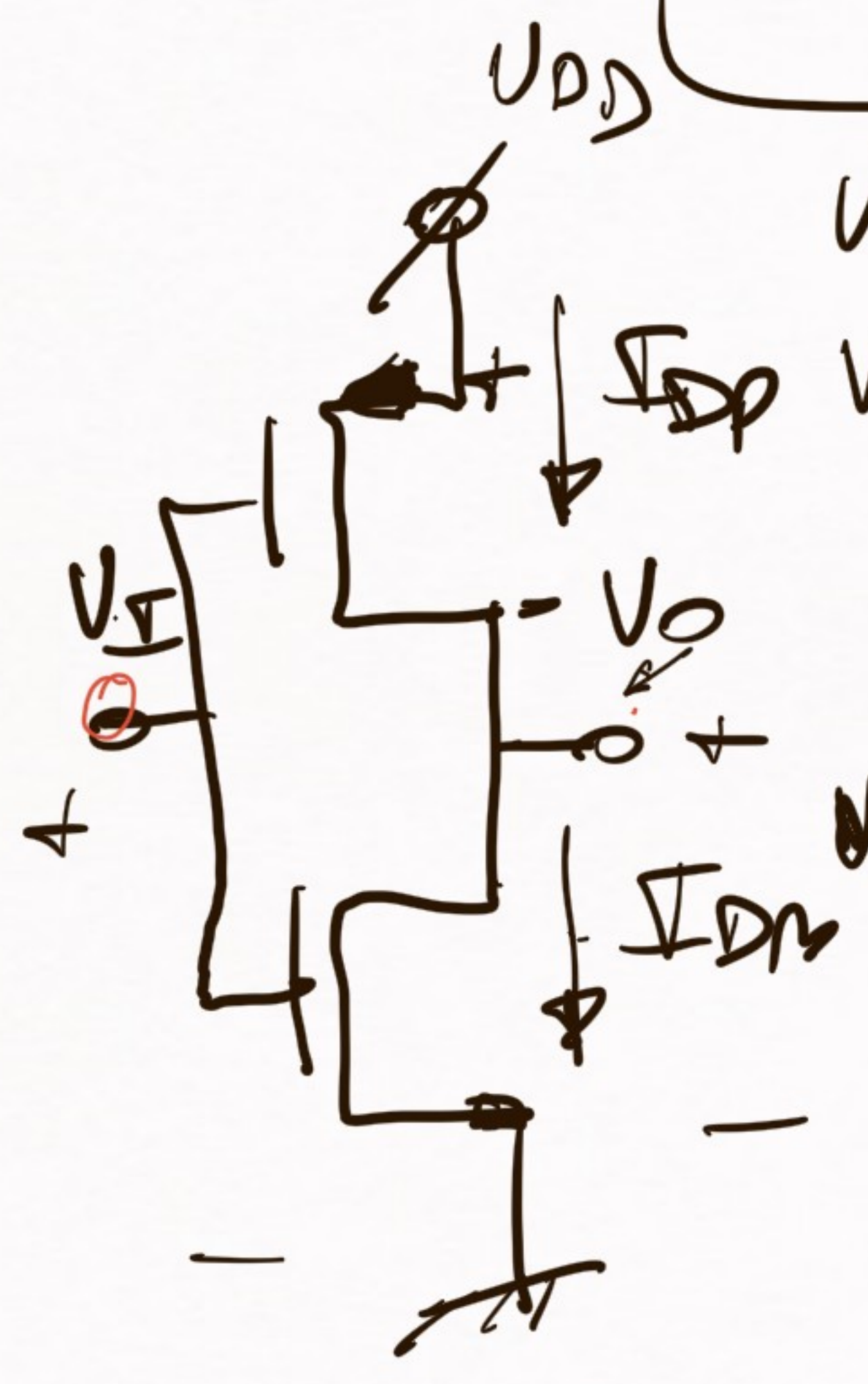
Idea básica:

$V_I = 0 \Rightarrow$ NMOS OFF, PMOS ON $\Rightarrow V_O = V_{DD}$
 $V_I = V_{DD} \Rightarrow$ NMOS ON, PMOS OFF $\Rightarrow V_O = 0$

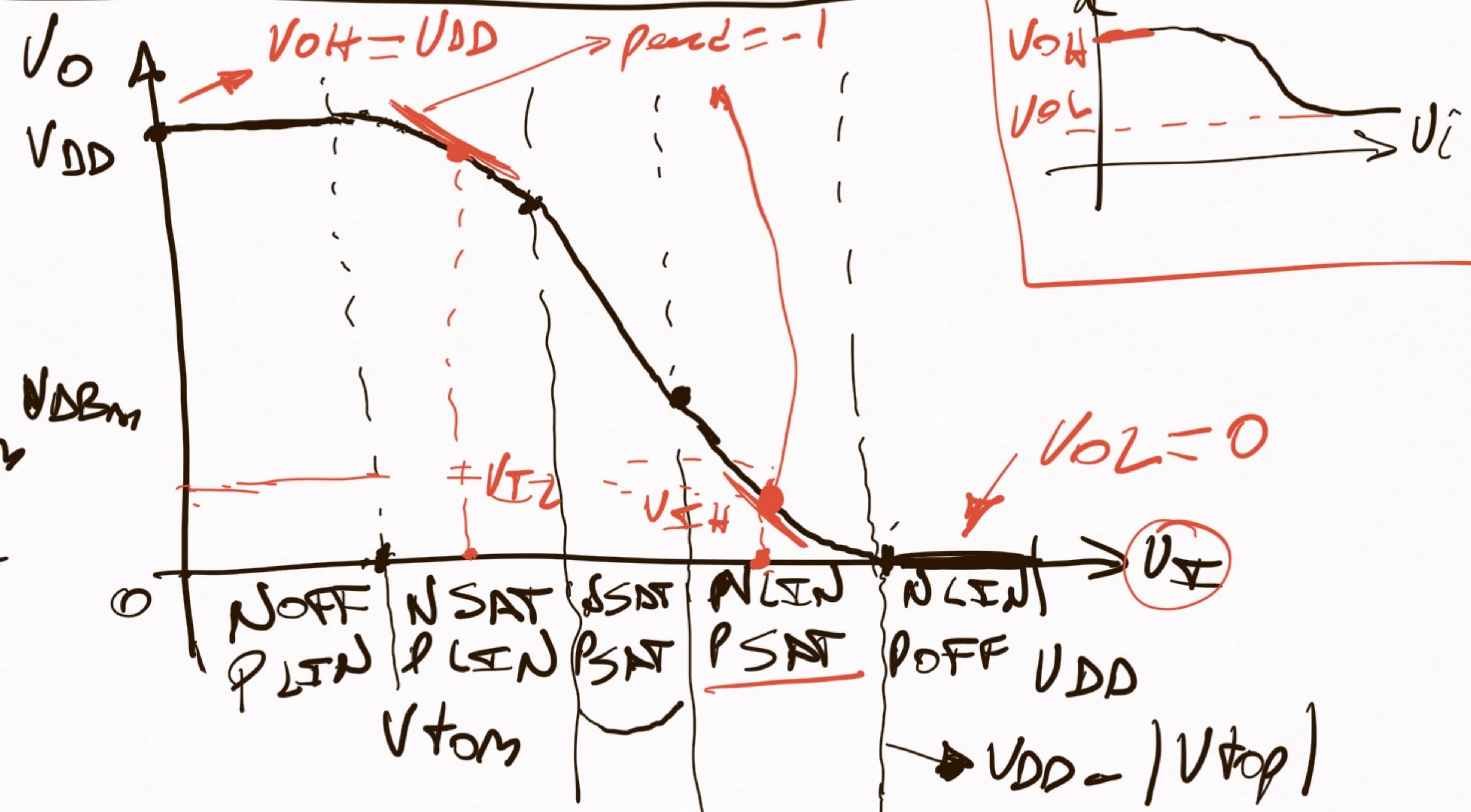
Propiedades fundamentales del inverso CMOS

- 1) $V_{OH} = V_{DD}$ y $V_{OL} = 0$ independiente del tamaño (w, l) de los transistores.
- 2) Se puede diseñar para tener una característica simétrica ($V_C = V_{DD}/2$)
→ amplios márgenes de ruido.
- 3) Idealmente el consumo estático es nulo
- 4) $R_i = \infty \Rightarrow$ característica estática independiente de los niveles de conexión a la salida

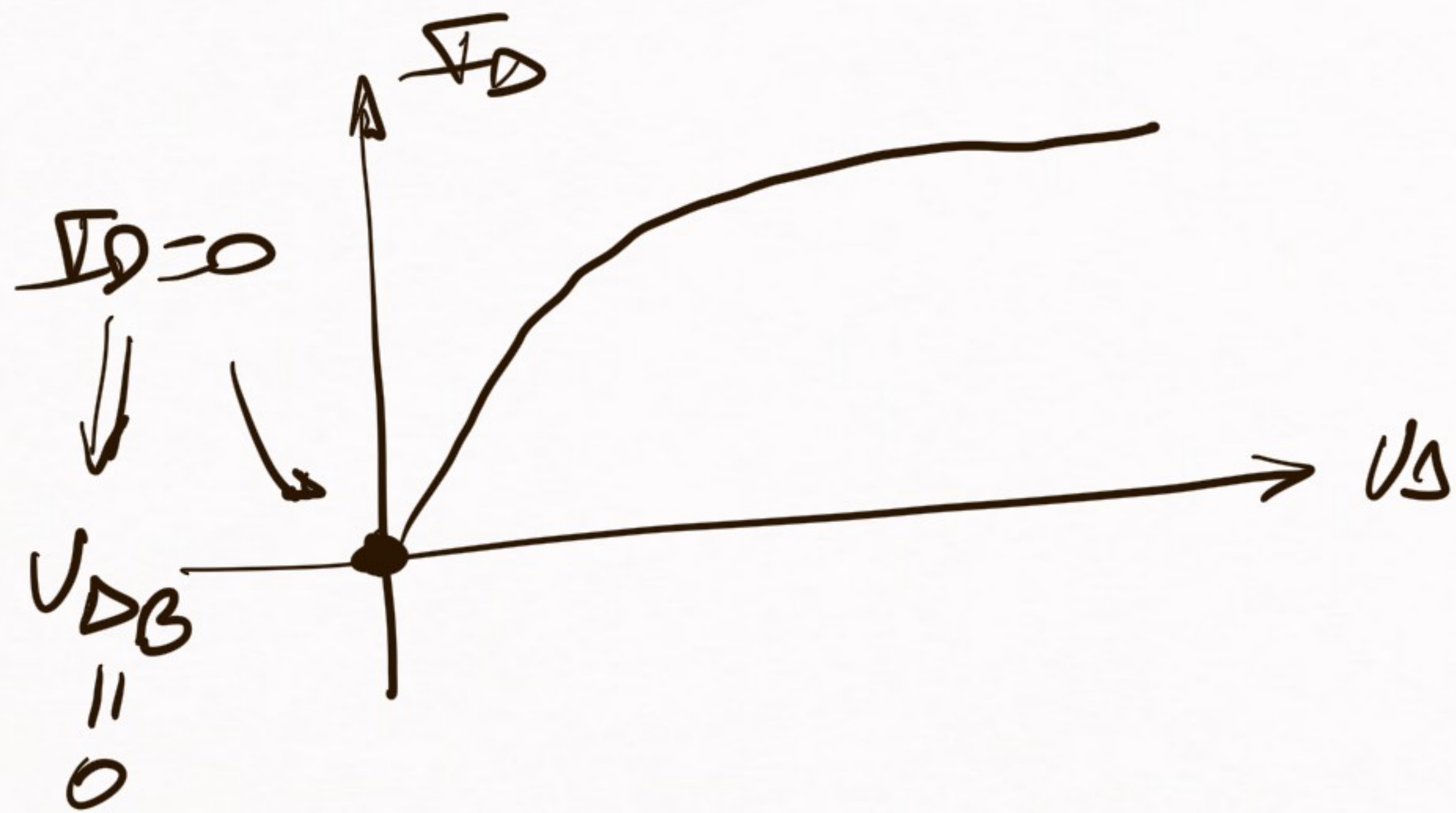
Característica estática del inversor CMOS



$I_{DN} = I_{DP}$



Si $V_{thn} = |V_{thp}|$ y $\beta_n = \beta_p$, $f_n = f_p$
 \Rightarrow característica es simétrica respecto a $V_o = V_i$
 y $V_C = V_{DD}/2$



NOFF

$$V_{SB} > V_P = \frac{V_{GB} - V_{th0n}}{1 + \beta}$$

III

0

$V_{GB} < V_{th0n}$

II

V_I

NSAT:

$$\left\{ \begin{array}{l} V_{SB} < V_P \iff V_{GB} > V_{th0n} \text{ requirito} \\ V_{DB} > V_P \iff V_{GS} > V_P = \frac{V_{GB} - V_{th0n}}{(1 + \beta)} \end{array} \right.$$

II

V_{GS}

Determinación de V_{IH}

⇒ zona en que I saturado y I en zona lineal.

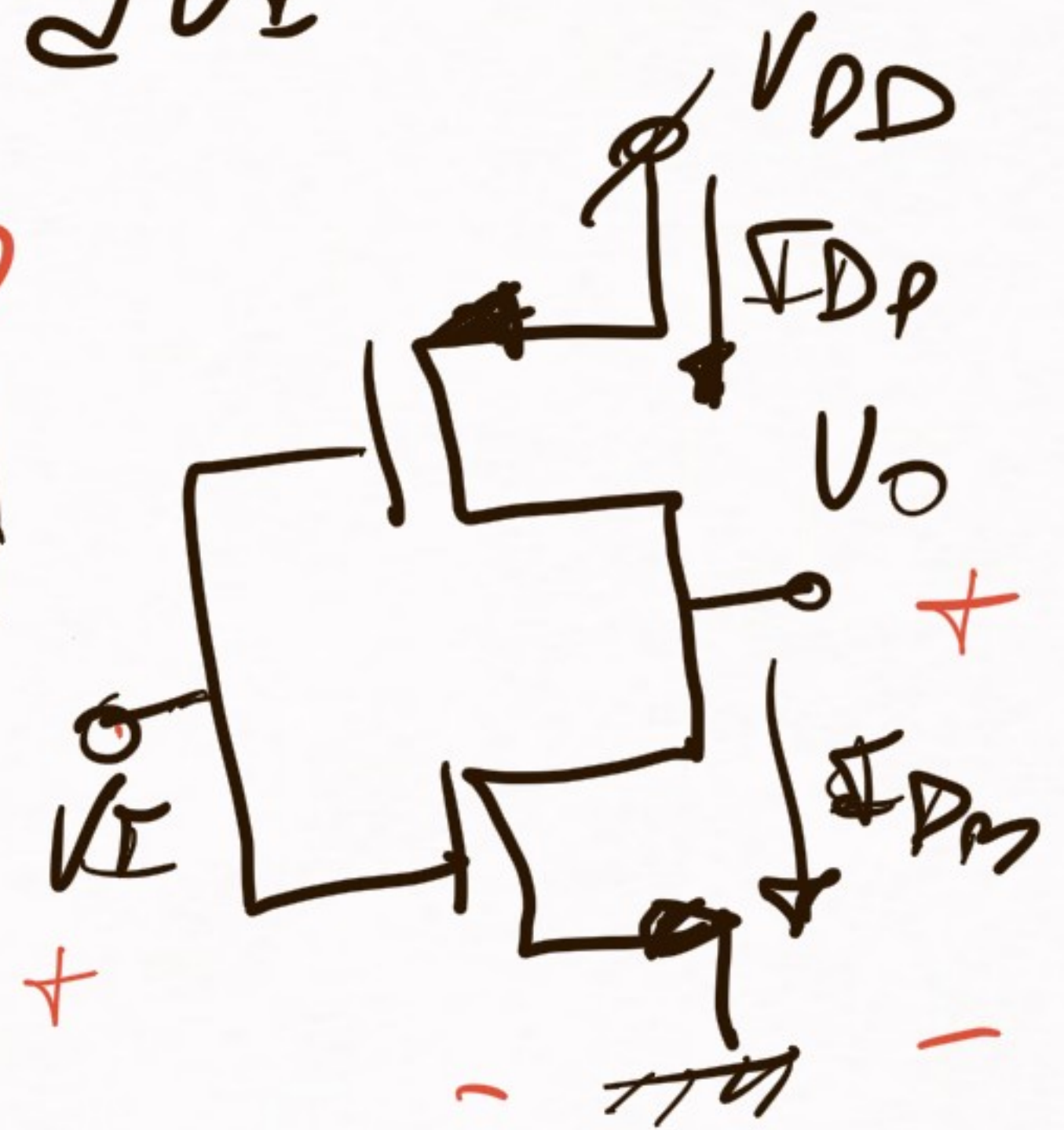
Caso simplificado y hay simetría: $\begin{cases} V_{top} = |V_{top}| = V_{to} \\ \beta_M = \beta_P = \beta \\ I_M = I_P = 0 \end{cases}$

⇒ $V_O = f(V_I)$ y determinar $V_I / \frac{dV_O}{dV_I} = -1$

$$I_{DM} = I_{DP}$$

$$I_{DM} = \beta (V_{G6} - V_{to}) (V_D - V_S) = \frac{1}{2} (V_D^2 - V_S^2)$$

$$I_{DP} = \frac{\beta}{2} (V_{B6} - V_{to})^2 = \frac{\beta}{2} (V_{DD} - V_I)^2$$



$$I_{SM} = I_{DP}$$

$$\Rightarrow \beta \left((V_{IE} - V_{to}) \cdot V_o - \frac{1}{2} V_o^2 \right) = \frac{\beta}{2} (V_{DD} - V_{IE} - V_{to})^2$$

$V_o = f(V_{IE})$
 y derivando ambos
 $V_{IE} / dV_o / dV_{IE} = -1$

(B) Derivar (I) a
 ambos lados de la
 igualdad respecto a
 V_{IE} .

$$V_o + (V_{IE} - V_{to}) \frac{dV_o}{dV_{IE}} - V_o \cdot \frac{dV_o}{dV_{IE}} = - (V_{DD} - V_{IE} - V_{to})$$

$$V_{IE} = V_{IH} / \frac{dV_o}{dV_{IE}} = -1$$

\Rightarrow substituir en (I)

$$\Rightarrow V_o |_{V_{IE} = V_{IH}} = V_{IH} - \frac{V_{DD}}{2}$$

$$\Rightarrow \boxed{V_{IH} = \frac{1}{8}(5V_{DD} - 2V_{th})}$$

Analogamente (o per simmetria)

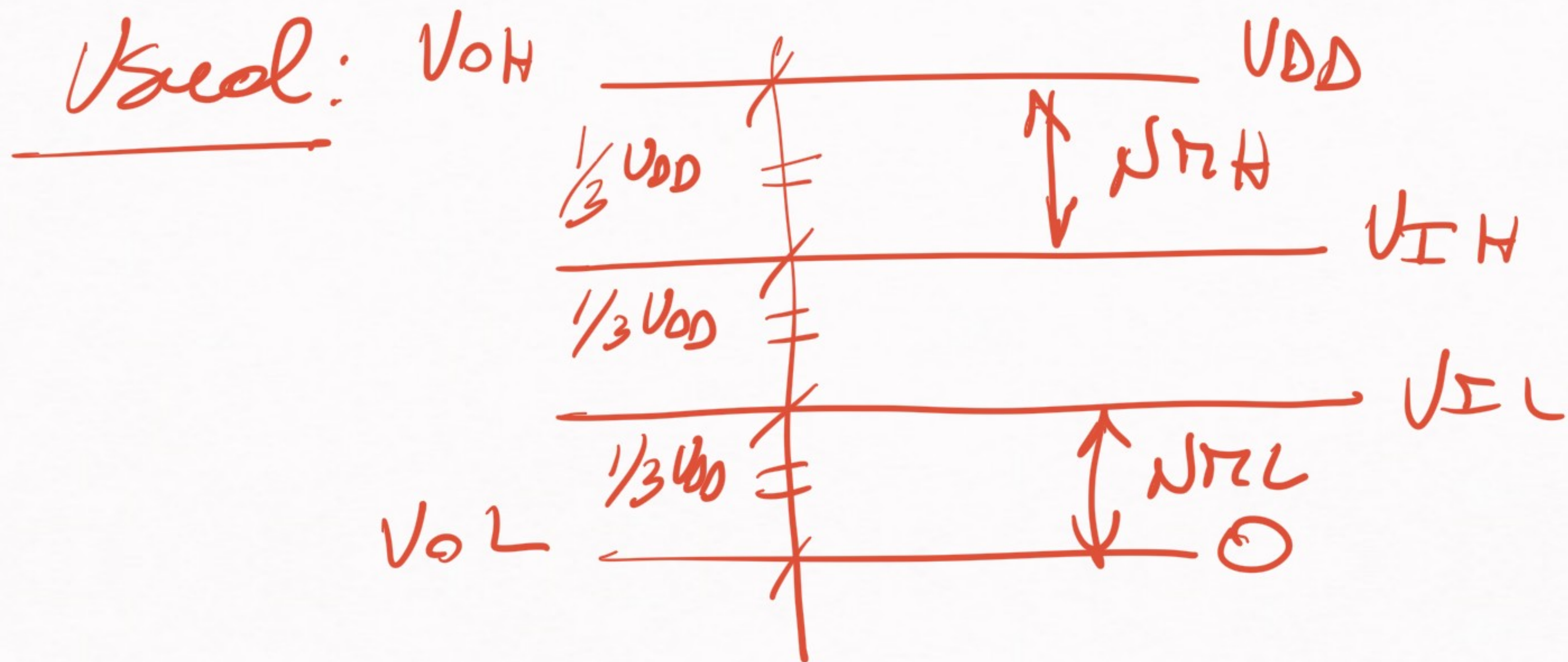
$$\Rightarrow \underline{V_{IL} = \frac{1}{8}(3V_{DD} + 2V_{th})}$$

$$\Rightarrow \text{NMH} = \underbrace{V_{OH}}_{V_{DD}} - \underbrace{V_{IH}}_0 = \frac{1}{8}(3V_{DD} + 2V_{th})$$

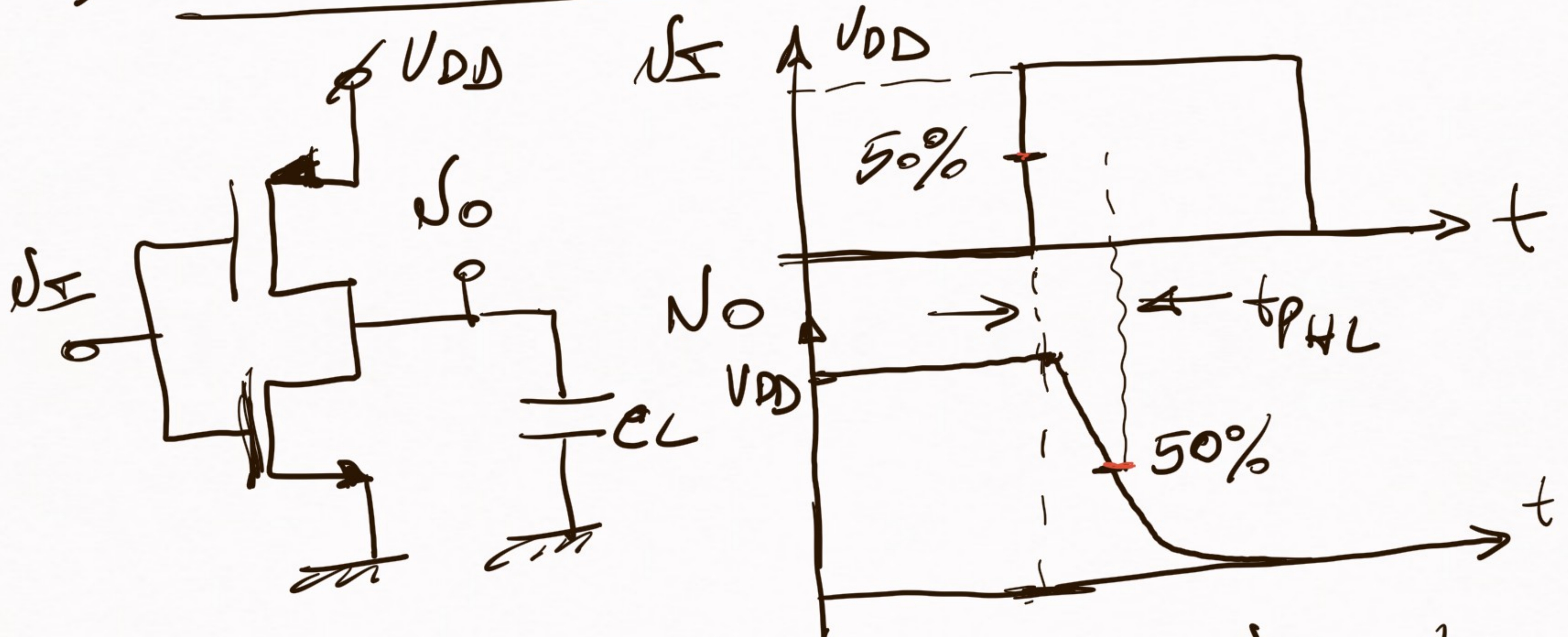
$$\Rightarrow \text{NML} = \underbrace{V_{IL}}_0 - \underbrace{V_{OL}}_0 = \underline{V_{IL} = \frac{1}{8}(3V_{DD} + 2V_{th})}$$

Es: $V_{DD} = 5V, V_{th} = 1V \Rightarrow V_{IL} = \text{NML} = \text{NMH} = \underline{2.1V}$

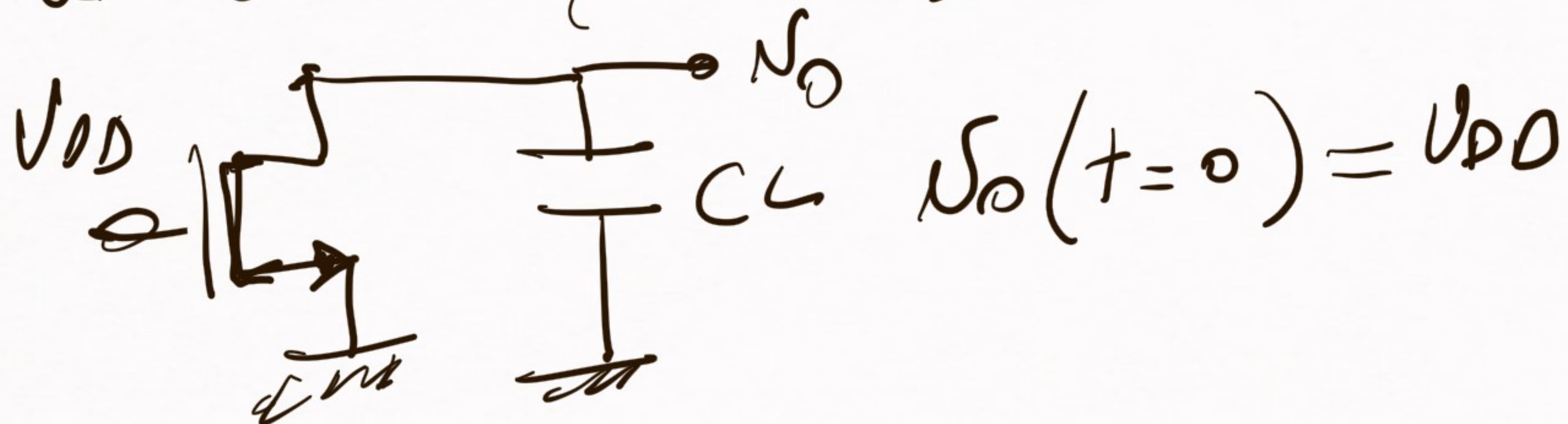
$$V_{IH} = 2.9V (= 5V - 2.1V) \quad // \quad \boxed{\text{Usuel: } \text{NML} = \text{NMH} = \frac{1}{3}V_{DD}}$$

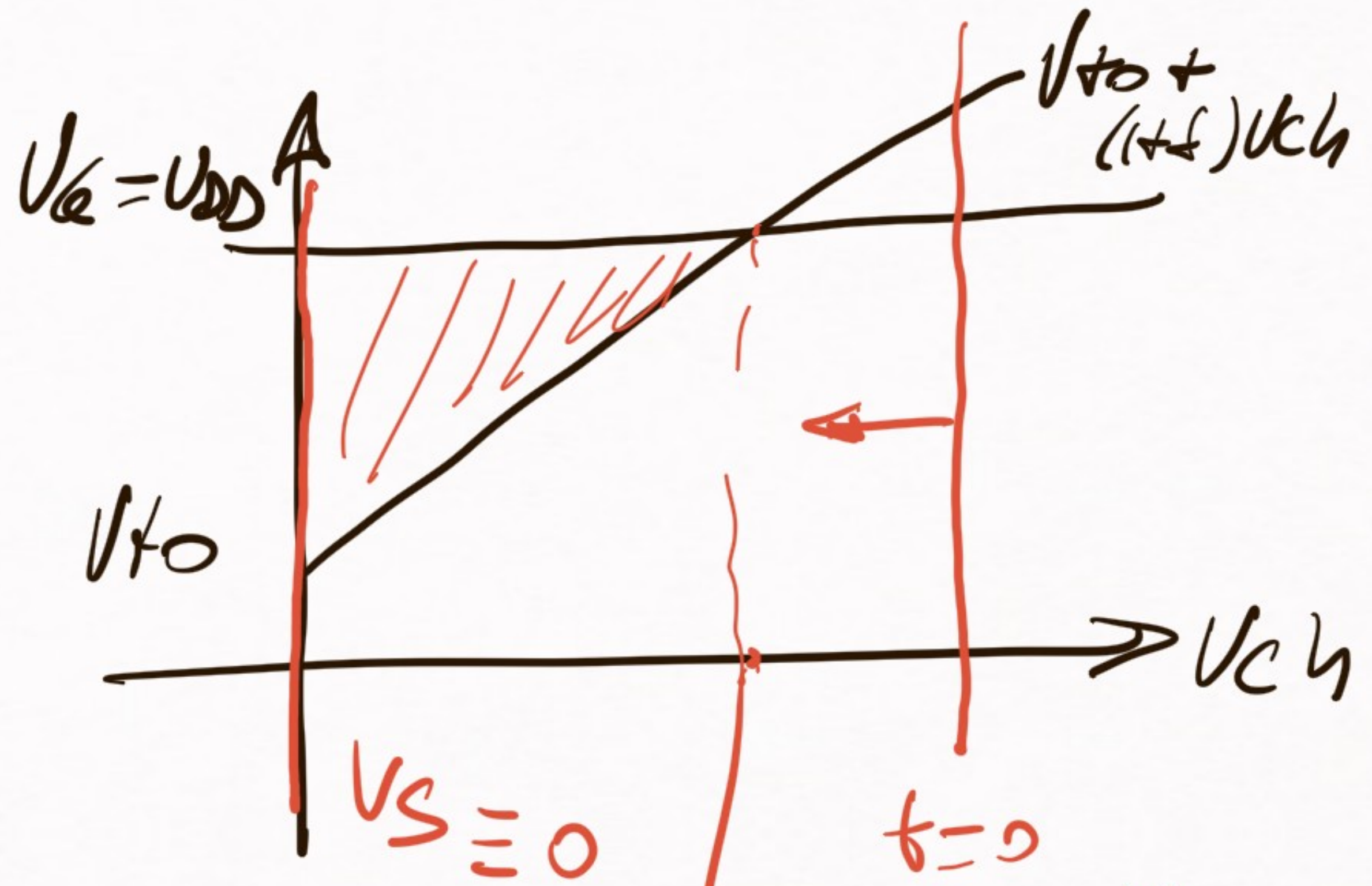
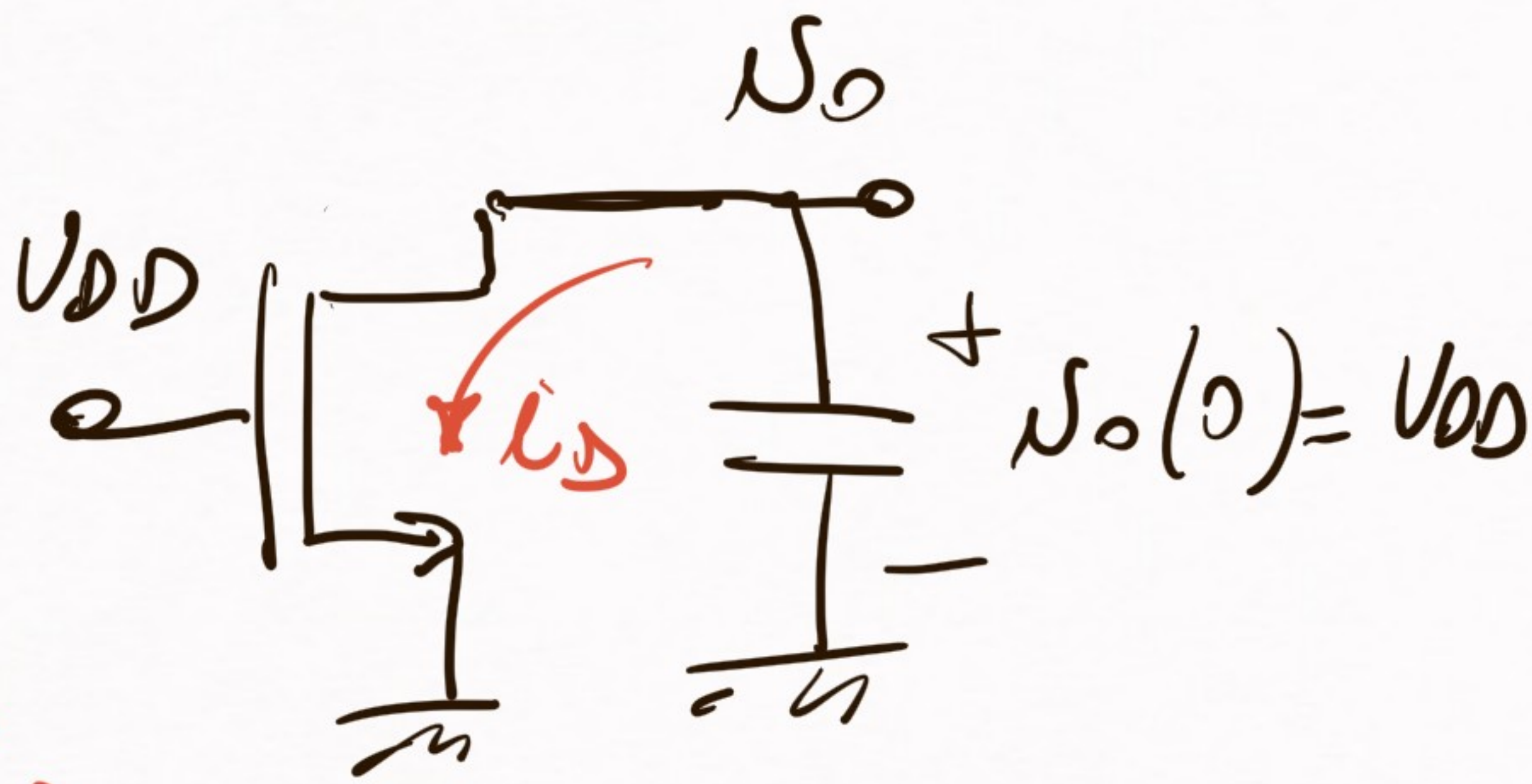


2) Velocidad, tiempo de Propagación



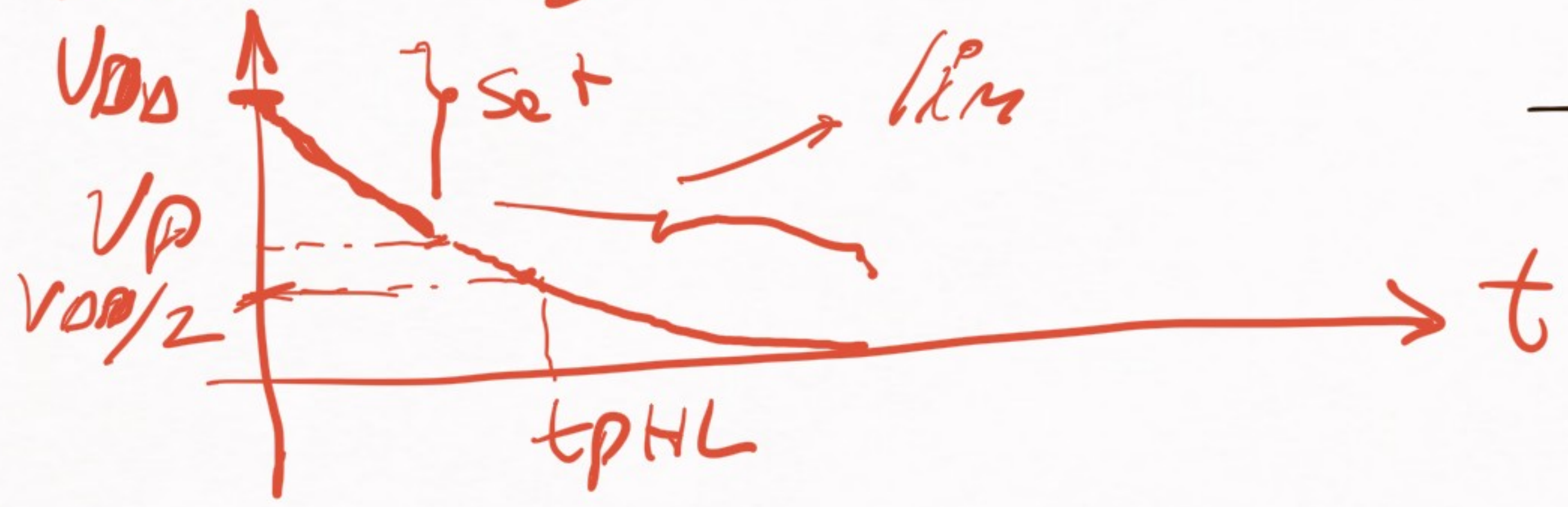
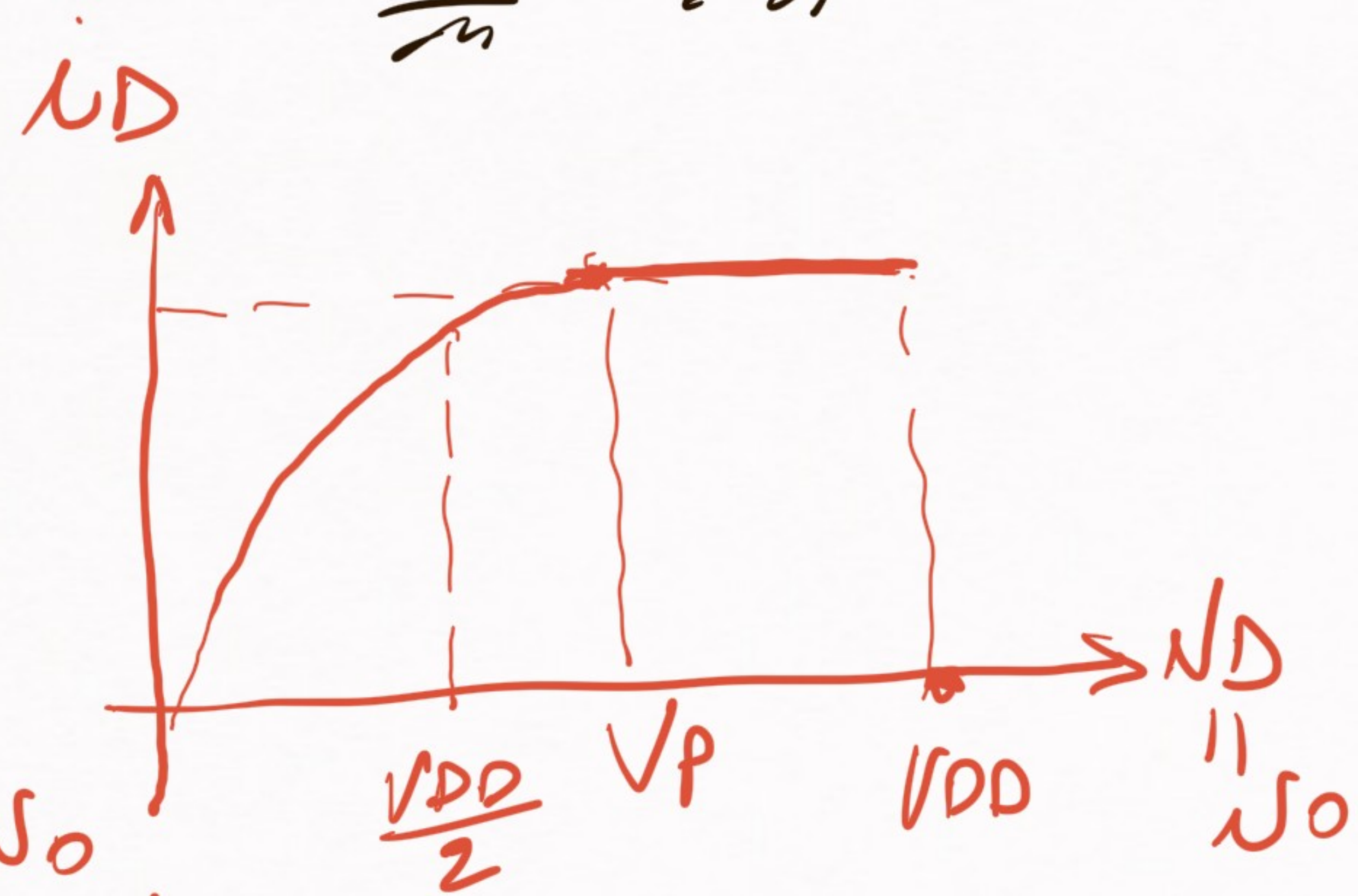
$V_I: 0 \rightarrow V_{DD} (V_I = V_{DD}) \Rightarrow P \text{ OFF, } N \text{ conduce}$





$$V_p = \frac{V_{ch} - V_{to}}{(1+d)} \mu S_{qt}$$

$$t_{PHL} = f\left(\mu, C_o, \frac{W}{L}, C_L, V_{DD}, V_{to}, d\right)$$



$$\Rightarrow t_{PHL} = f\left(\mu_n \cdot \frac{W}{L}, V_{th}, f, C_L, V_{DD}\right)$$

Si $V_{th} = \frac{1}{5} V_{DD}$ (relación aprox. usual en muchas tecnologías)

$f_d = 0$

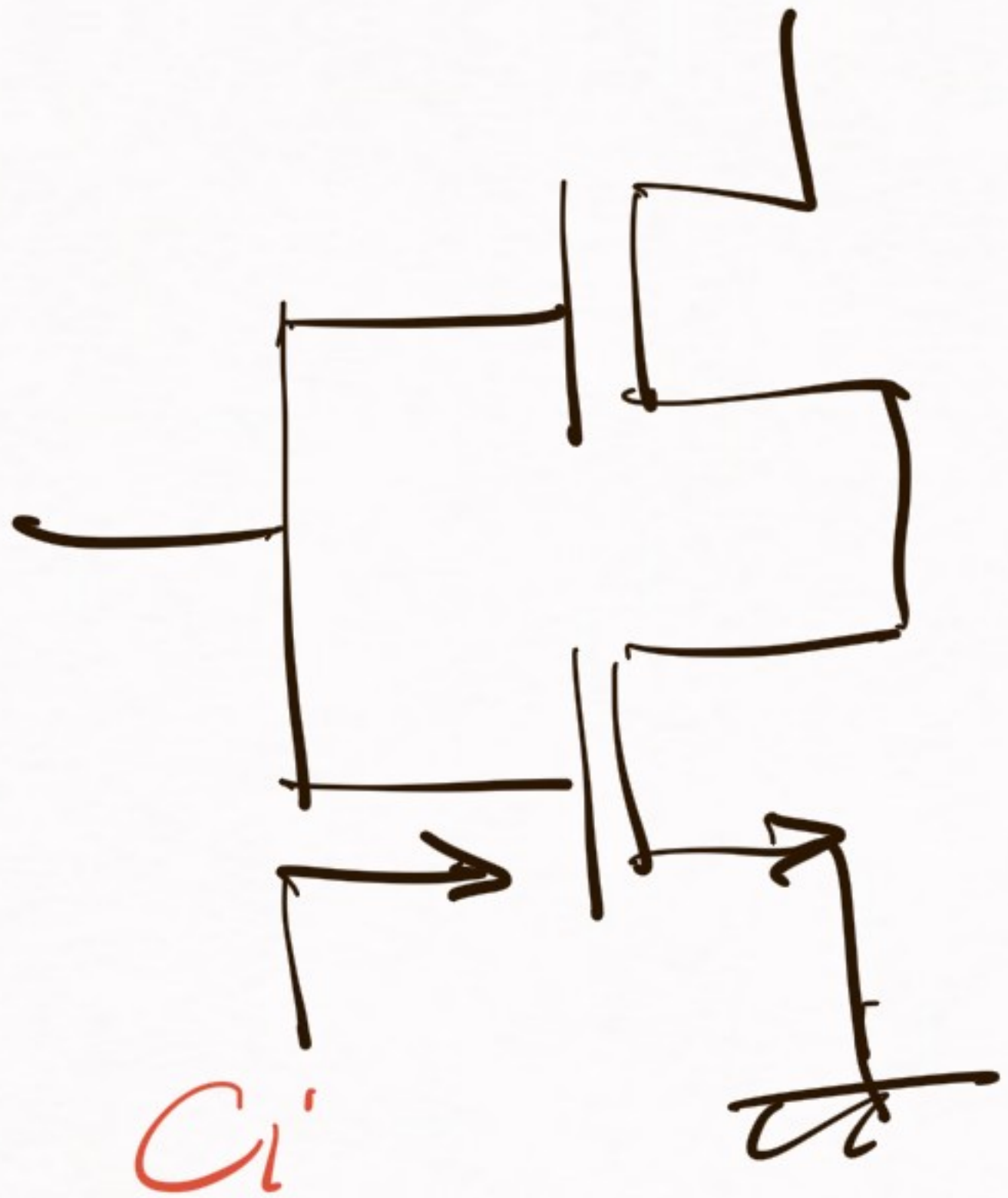
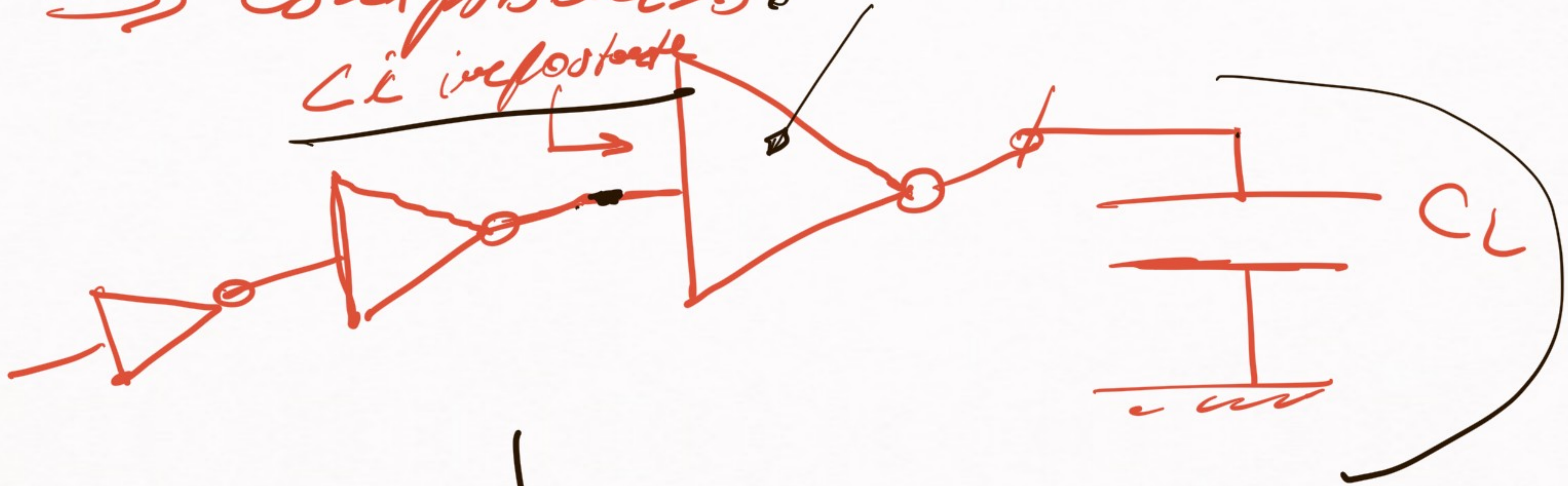
$$t_{PHL} \approx \frac{1.6 \cdot C_L}{\underbrace{\mu_n \frac{W}{L}}_{\beta_n} \cdot V_{DD}}$$

$$t_{PHL} \propto C_L \quad || \quad t_{PHL} \propto \frac{1}{V_{DD}} \quad || \quad t_{PHL} \propto \frac{1}{\left(\frac{W}{L}\right)_n}$$

$\left(\frac{W}{L}\right) \uparrow \Rightarrow I_{on} \uparrow \Rightarrow t_{PHL} \downarrow$ pero \Rightarrow sube C_L
de las etapas posteriores

⇒ Comproviso:

C_i impostate



$C_i \propto w \cdot L \cdot C'_{ox}$
 $\frac{\epsilon_{ox} \cdot t_{ox}}$

